TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRIAC

TLP3061(S),TLP3062(S),TLP3063(S)

OFFICE MACHINE
HOUSEHOLD USE EQUIPMENT
TRIAC DRIVER
SOLID STATE RELAY

The TOSHIBA TLP3061 (S), TLP3062 (S), TLP3063 (S) consist of a zero voltage crossing turn-on photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

• Peak Off-State Voltage : 600 V (min)

• Trigger LED Current : 15 mA (max) (TLP3061(S))

10 mA (max) (TLP3062(S)) 5 mA (max) (TLP3063(S))

On-State Current : 100 mA (max)
 Isolation Voltage : 5000 Vrms (min)

• UL Recognized : UL1577, File No. E67349

• SEMKO Approved : SS EN60065

SS EN60950, File No.9841113

BSI Approved : BS EN60065, File No.8385
 BS EN60950, File No.8386

• Option (D4) type

VDE approved: DIN EN60747-5-2

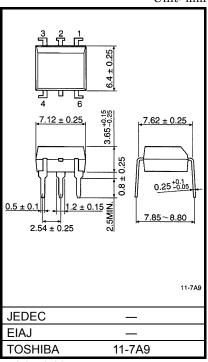
Approved No. 40009302

Maximum operating insulation voltage: 890 VpK Highest permissible over voltage: 8000 VpK

(Note):When a EN60747-5-2 approved type is needed, please designate the "Option (D4)"

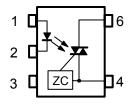
• Construction mechanical rating

	7.62 mm pich Standard Type	10.16 mm pich TLPxxxxF type
Creepage Distance	7.0 mm (Min)	8.0 mm (Min)
Clearance	7.0 mm (Min)	8.0 mm (Min)
Insulation Thickness	0.5 mm (Min)	0.5 mm (Min)



weight: 0.39g

Pin Configuration (top view)



- 1: Anode
- 2: Cathode
- 3: N.C.
- 4:Terminal 1
- 6:Terminal 2

ZC:Zero-cross Circuit



Absolute Maximum Ratings (Ta = 25°C)

Characteristic			Symbol	Rating	Unit
	Forward current	lF	50	mA	
LED	Forward current derating (Ta ≥ 53°	ΔI _F / °C	-0.7	mA / °C	
	Peak forward current (100 µs pulse, 100 pps)	I _{FP}	1	А	
	Power dissipation		P_{D}	100	mW
	Power dissipation derating (Ta ≥ 2	5°C)	ΔP _D / °C	-1.0	mW / °C
	Reverse voltage		V_{R}	5	V
	Junction temperature	Тj	125	°C	
	Off-state output terminal voltage	V_{DRM}	600	V	
	On-state RMS current	Ta = 25°C	l=	100	mΛ
		Ta = 70°C	IT(RMS)	50	- mA
	On–state current derating (Ta ≥ 25	ΔI _T / °C	-1.1	mA / °C	
Detector	Peak on–state current (100µs pulse, 120 pps)	I _{TP}	2	А	
De	Peak nonrepetitive surge current (P _W = 10 ms, DC = 10%)	I _{TSM}	1.2	А	
	Power dissipation	P_{D}	300	mW	
	Power dissipation derating (Ta ≥ 2	ΔP _D / °C	-4.0	mW / °C	
	Junction temperature	Tj	115	°C	
Storage	e temperature range		T _{stg}	-55~150	°C
Operat	ing temperature range	T _{opr}	-40~100	°C	
Lead soldering temperature (10 s)			T _{sol}	260	°C
Total p	ackage power dissipation	PT	330	mW	
Total package power dissipation derating (Ta ≥ 25°C)			ΔP _T / °C	-4.4	mW / °C
	Isolation voltage (AC, 1 min., R.H.≤ 60%) (Note 1)			5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4 and 6 shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V_{AC}	_	_	240	Vac
Forward current	l _F *	15	20	25	mA
Peak on-state current	I _{TP}	_	_	1	Α
Operating temperature	T _{opr}	-25	_	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

In the case of TLP3062



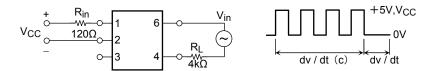
Individual Electrical Characteristics (Ta = 25°C)

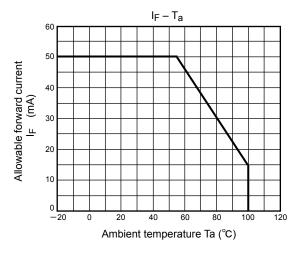
	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V _F	I _F = 10 mA	1.0	1.15	1.3	V
ED	Reverse current	I _R	V _R = 5 V	_	_	10	μA
	Capacitance	C _T	V = 0, f = 1 MHz	_	10	_	pF
	Peak off-state current	I _{DRM}	V _{DRM} = 600 V	_	10	1000	nA
	Peak on-state voltage	V _{TM}	I _{TM} = 100 mA	_	1.7	3.0	V
tor	Holding current	lΗ	_	_	0.6	_	mA
Detector	Critical rate of rise of off–state voltage	dv / dt	V _{in} = 240 Vrms, Ta = 85°C (Fig.1) 200	500	_	V / µs
	Critical rate of rise of commutating voltage	dv / dt (c)	V _{in} = 60 Vrms, I _T = 15mA (Fig.1) –	0.2	_	V / μs

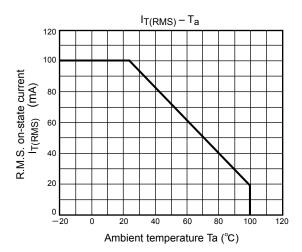
Coupled Electrical Characteristics (Ta = 25°C)

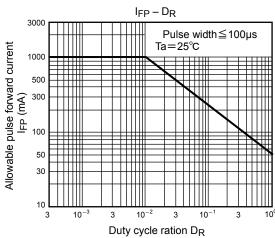
Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit	
Trigger LED current	TLP3061(S)	l _{FT}	V _T = 6 V	_	_	15	mA	
	TLP3062(S)			_	5	10		
	TLP3063(S)			_	_	5		
Inhibit voltage	•	V _{IH}	I _F = rated I _{FT}	_	_	50) V	
Leakage in inhibited state		l _{IH}	I _F = rated I _{FT} V _T = rated V _{DRM}	_	100	300	μΑ	
Capacitance input to outp	out	CS	V _S = 0, f = 1 MHz	_	0.8	_	pF	
Isolation resistance		R _S	V _S = 500 V (R.H.≤ 60%)	5×10 ¹⁰	10 ¹⁴	-	Ω	
Isolation voltage		BVS	AC, 1 minute	5000	_	_	Vrms	
			AC, 1 second, in oil	_	10000	_		
			DC, 1 minute, in oil	_	10000	_	V _{dc}	

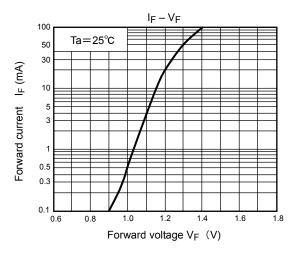
Fig. 1 dv / dt test circuit

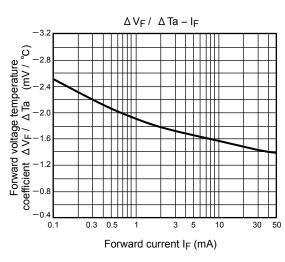


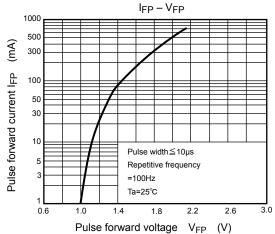


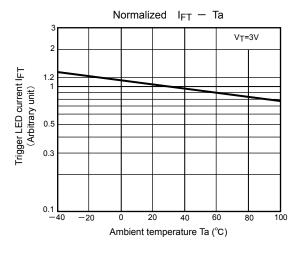


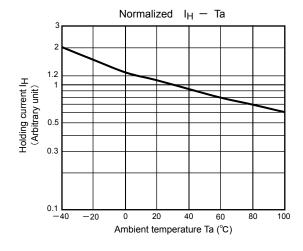


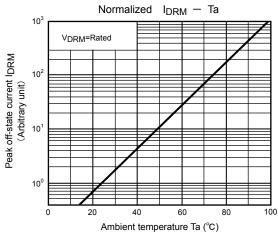


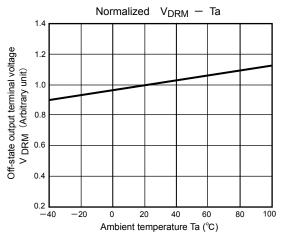


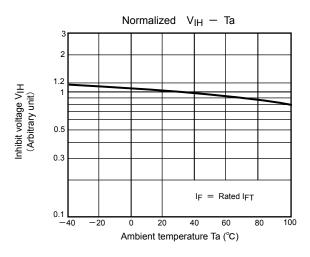


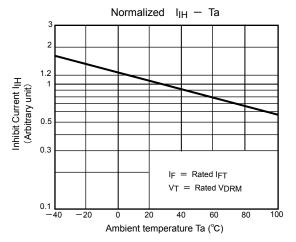












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